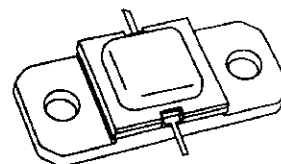


RF & MICROWAVE TRANSISTORS S-BAND RADAR APPLICATIONS

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- 5:1 VSWR CAPABILITY
- LOW THERMAL RESISTANCE
- INPUT/OUTPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- $P_{OUT} = 5.0 \text{ W MIN. WITH } 5.2 \text{ dB GAIN}$



.400 x .400 2NLFL (S042)
hermetically sealed

ORDER CODE
AM83135-005

BRANDING
83135-5

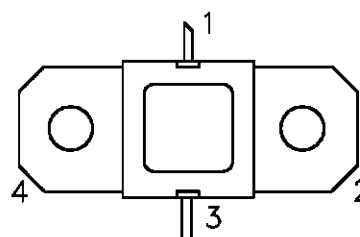
DESCRIPTION

The AM83135-005 device is a medium power silicon bipolar NPN transistor specifically designed for S-Band radar pulsed driver applications.

This device is capable of operation over a wide range of pulse widths, duty cycles and temperatures, and can withstand a 5:1 output VSWR. Low RF thermal resistance, refractory/gold metallization, and computerized automatic wire bonding techniques ensure high reliability and product consistency.

The AM83135-005 is supplied in the AMPAC™ Hermetic Metal/Ceramic package with internal Input/Output matching circuitry, and is intended for military and other high reliability applications.

PIN CONNECTION



1. Collector 3. Emitter
2. Base 4. Base

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation* ($T_C \leq 100^{\circ}\text{C}$)	40	W
I_C	Device Current*	1.8	A
V_{CC}	Collector-Supply Voltage*	34	V
T_J	Junction Temperature (Pulsed RF Operation)	250	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +200	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	3.75	$^{\circ}\text{C/W}$
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*Applies only to rated RF amplifier operation

ELECTRICAL SPECIFICATIONS ($T_{\text{case}} = 25^{\circ}\text{C}$)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_{\text{C}} = 4 \text{ mA}$	$I_{\text{E}} = 0 \text{ mA}$	50	—	—	V
BV_{EBO}	$I_{\text{E}} = 2 \text{ mA}$	$I_{\text{C}} = 0 \text{ mA}$	3.5	—	—	V
BV_{CER}	$I_{\text{C}} = 4 \text{ mA}$	$R_{\text{BE}} = 10 \ \Omega$	50	—	—	V
I_{CES}	$V_{\text{CE}} = 30 \text{ V}$		—	—	2.0	mA
h_{FE}	$V_{\text{CE}} = 5 \text{ V}$	$I_{\text{C}} = 500 \text{ mA}$	10	—	—	—

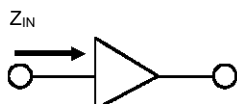
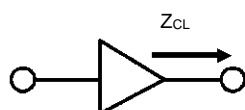
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 3.1 - 3.5 \text{ GHz}$	$P_{\text{IN}} = 1.5 \text{ W}$	$V_{\text{CC}} = 30 \text{ V}$	5.0	6.0	—	W
h_{c}	$f = 3.1 - 3.5 \text{ GHz}$	$P_{\text{OUT}} = 5.0 \text{ W}$	$V_{\text{CC}} = 30 \text{ V}$	27	—	—	%
P_{G}	$f = 3.1 - 3.5 \text{ GHz}$	$P_{\text{OUT}} = 5.0 \text{ W}$	$V_{\text{CC}} = 30 \text{ V}$	5.2	6.4	—	dB

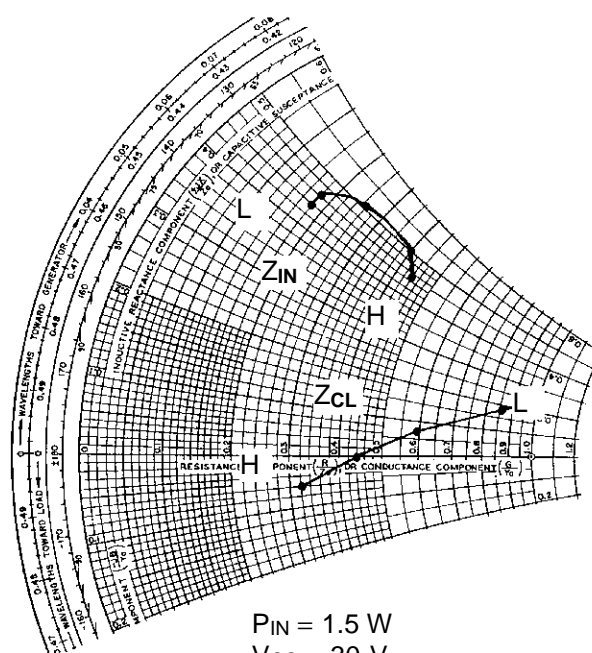
Note: Pulse Width = $100 \mu\text{s}$

Duty Cycle = 10%

IMPEDANCE DATA

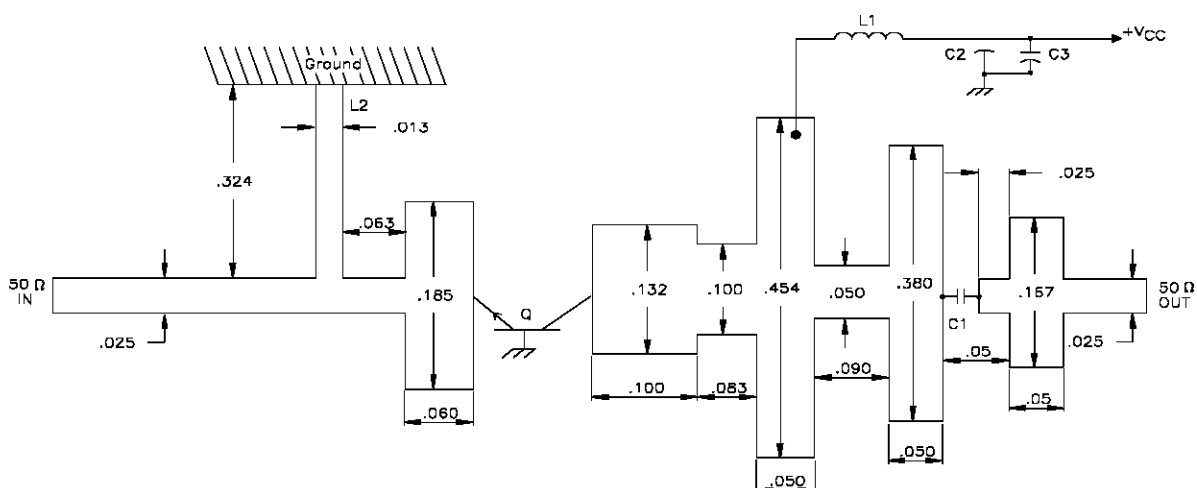
TYPICAL INPUT
IMPEDANCETYPICAL COLLECTOR
LOAD IMPEDANCE

FREQ.	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
L = 2.7 GHz	$9.0 + j 22.0$	$48.0 + j 11.5$
U = 2.9 GHz	$9.0 + j 23.0$	$43.0 + j 9.0$
M = 3.1 GHz	$12.5 + j 25.0$	$30.0 + j 3.0$
U = 3.3 GHz	$20.0 + j 25.0$	$21.5 + j 0.0$
H = 3.5 GHz	$22.0 + j 22.5$	$16.0 - j 3.0$



$P_{IN} = 1.5 \text{ W}$
 $V_{CC} = 30 \text{ V}$
 Normalized to 50 ohms

TEST CIRCUIT



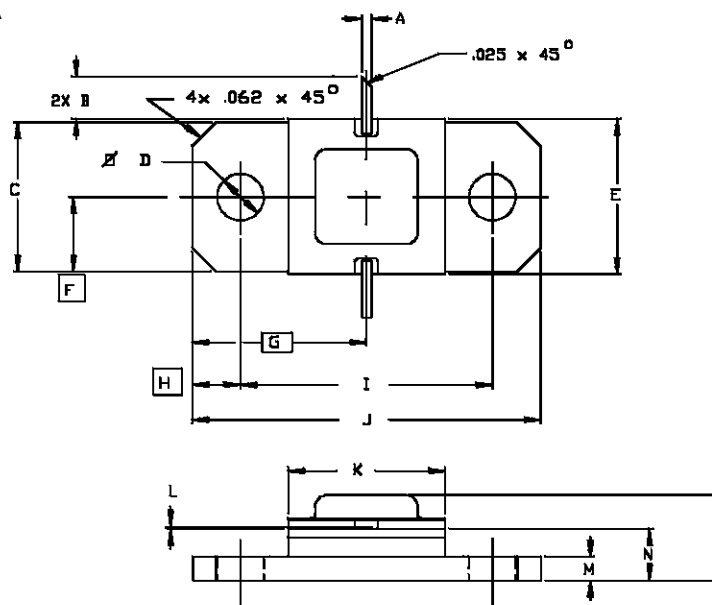
All dimensions are in inches.
 Substrate Material: .025 tick Al₂O₃ (Er = 9.6)

C1 : 100 pF Chip Capacitor
 (Note: Mounted on its thin side)
 C2 : 1500 pF RF Feedthru
 C3 : 100 mF Electrolytic

L1 : No. 32 Wire, 2 Turns 1/16" I.D.
 L2 : Printed Choke

PACKAGE MECHANICAL DATA

Ref.: Dwg. No. 12-0213 rev. A
UDCS Doc. No. 1011416



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.020/0,51	.030/0,76	K	.395/10,03	.415/10,54
B	.100/2,54		L	.004/0,10	.006/0,18
C	.376/9,55	.396/10,06	M	.052/1,32	.072/1,83
D	.110/2,79	.130/3,30	N	.118/3,00	.131/3,33
E	.395/10,03	.407/10,34	P		.230/5,84
F	.193/4,90				
G	.450/11,43				
H	.125/3,18				
I	.640/16,26	.660/16,76			
J	.890/22,61	.910/23,11			

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